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TOSHIBA Photocoupler GaAs Ired & Photo-Triac

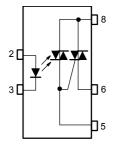
TLP3506

Triac Driver **Programmable Controllers** AC-Output Module Solid State Relay

The TOSHIBA TLP3506 consists of a photo-triac optically coupled to a gallium arsenide infrared emitting diode in a 8 lead plastic DIP.

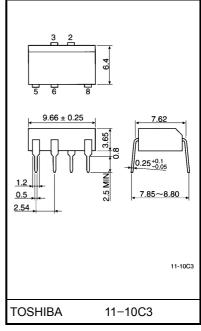
- Peak off-state voltage: 600 V (min.) •
- Trigger LED current: 10 mA (max.) .
- On-state current: 0.5Arms (max.) ٠
- Isolation voltage: 2500 V_{rms} (min.)
- UL recoguized: UL1577, file no. E67349

Pin Configuration (top view)



2 : ANODE 3 : CATHODE 5 : TRIAC GATE 6 : TRIAC T1 8 : TRIAC T2

Unit in mm



Weight: 0.52 g

Maximum Ratings (Ta = 25°C)

Characteristic			Symbol	Rating	Unit	
	Forward current		١ _F	50	mA	
	Forward current derating (Ta ≥ 53	°C)	ΔI _F / °C	-0.7	mA / °C	
LED	Peak forward current (100 µs pulse, 100 pps)		I _{FP}	1	А	
	Reverse voltage	V _R	5	V		
	Junction temperature	Тј	125	°C		
	Off-state output terminal voltage)ff-state output terminal voltage		600	V	
	On-state RMS current	Ta = 40°C		0.5	А	
<u>ب</u>		Ta = 60°C	I _{T(RMS)}	0.35	~	
Detector	On–state current derating (Ta ≥ 40°C)		ΔI _T / °C	-7.2	mA / °C	
Det	Peak current from snubber circuit (100µs pulse, 120 pps)	I _{SP}	2	А		
	Peak nonrepetitive surge current (ITSM	5	А		
	Junction temperature	Тј	110	°C		
Storag	Storage temperature range			-40~125	°C	
Operat	Operating temperature range			-20~80	°C	
Lead soldering temperature (10 s)			T _{sol}	260	°C	
Isolation voltage (AC, 1 min., R.H.≤ 60%) (Note)			BVS	2500	V _{rms}	

(Note)Device considered a two terminal: LED side pins shorted together and detector side pins shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{AC}	_	_	240	Vac
Forward current	١ _F	15	20	25	mA
Peak current from snubber circuit	I _{SP}	_	_	1	А
Operating temperature	T _{opr}	-20	_	80	°C

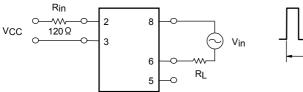
Individual Electrical Characteristics (Ta = 25°C)

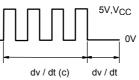
Characteristic		Symbol	Test Condition	Min.	Тур.	Max.	Unit
LED	Forward voltage	VF	I _F = 10 mA	1.0	1.15	1.3	V
	Reverse current	I _R	V _R = 5 V		_	10	μA
	Capacitance	CT	V = 0, f = 1 MHz	_	30	_	pF
Detector	Peak off-state current	I _{DRM}	V _{DRM} = 600 V, Ta = 110°C	_	—	100	μA
	Peak on-state voltage	V _{TM}	I _{TM} = 0.75 A	_	—	3.0	V
	Holding current	Ι _Η	—		—	25	mA
	Critical rate of rise of off–state voltage	dv / dt	V _{in} = 240 V _{rms} (Fig.1)		500	_	V / µs
	Critical rate of rise of commutating voltage	dv / dt (c)	V _{in} = 240 V _{rms} , I _T = 0.5 A _{rms} (Fig.1)	_	5	_	V / µs

Coupled Electrical Characteristics (Ta = 25°C)

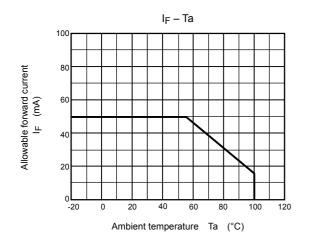
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Trigger LED current	I _{FT}	V _T = 6 V	_	_	10	mA
Capacitance (input to output)	C _S	V _S = 0, f = 1 MHz	—	1.5	_	pF
Isolation resistance	R _S	V _S = 500 V	5×10 ¹⁰	10 ¹⁴	_	Ω
	BVS	AC, 1 minute	2500	_	_	V _{rms}
Isolation voltage		AC, 1 second, in oil	—	5000	_	
		DC, 1 minute, in oil	—	5000	—	V _{dc}

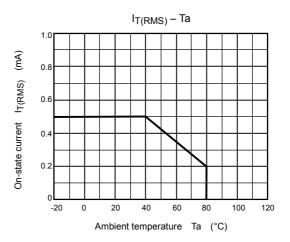
Fig.1: dv / dt test circuit

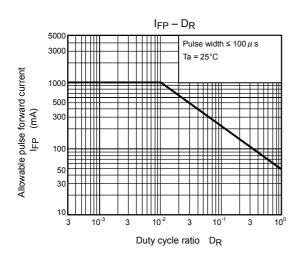


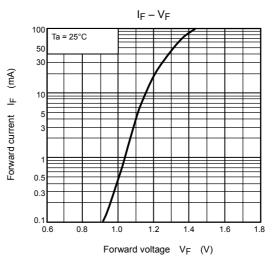


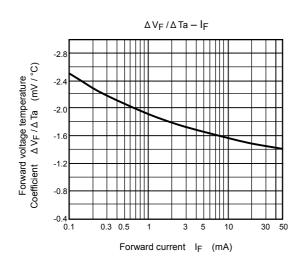
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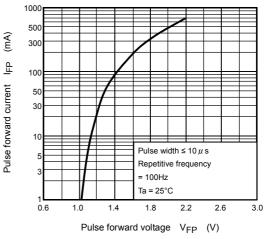


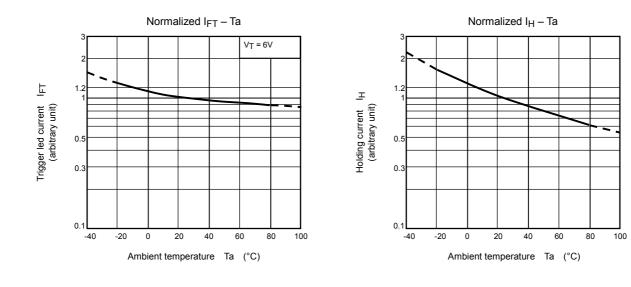




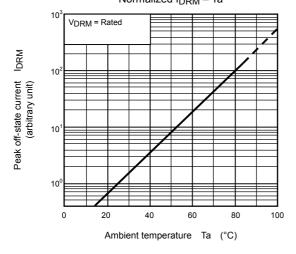


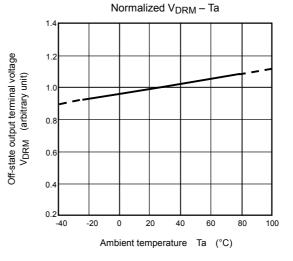
 $I_{FP} - V_{FP}$

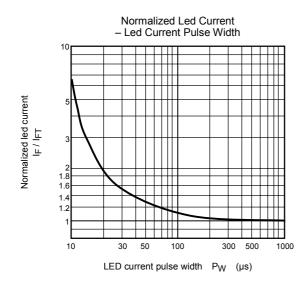




Normalized I_{DRM} – Ta







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000707EBC

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